

FDN5618P_G-VB Datasheet

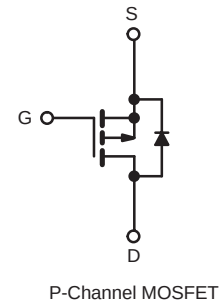
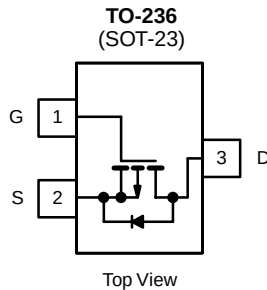
P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 60	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	0.05
Q_g (Max.) (nC)	12	
Q_{gs} (nC)	3.8	
Q_{gd} (nC)	5.1	
Configuration	Single	

FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV_{RMS} (t = 60 s; f = 60 Hz)
- Sink to Lead Creepage Distance = 4.8 mm
- P-Channel
- 175 °C Operating Temperature
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available


RoHS*
 COMPLIANT


ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	- 21	
Linear Derating Factor		0.18	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	120	mJ
Repetitive Avalanche Current ^a	I_{AR}	- 5.2	A
Repetitive Avalanche Energy ^a	E_{AR}	2.7	mJ
Maximum Power Dissipation	P_D	27	W
Peak Diode Recovery dV/dt ^c	dV/dt	- 4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	
Mounting Torque	6-32 or M3 screw	10 1.1	

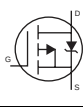
Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25$ V, starting $T_J = 25$ °C, L = 5.0 mH, $R_G = 25$ Ω , $I_{AS} = -5.3$ A (see fig. 12).
- $I_{SD} \leq -6.7$ A, dI/dt ≤ 90 A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	5.5	

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		- 60	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = - 1 mA		-	- 0.060	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		- 1.0	-	- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V		-	-	- 100	μA
		V _{DS} = - 48 V, V _{GS} = 0 V, T _J = 150 °C		-	-	- 500	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 3.2 A ^b	-	0.05	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = - 25 V, I _D = - 3.2 A ^b		1.6	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1.0 MHz, see fig. 5		-	270	-	pF
Output Capacitance	C _{oss}			-	170	-	
Reverse Transfer Capacitance	C _{rss}			-	31	-	
Drain to Sink Capacitance	C	f = 1.0 MHz		-	12	-	
Total Gate Charge	Q _g	V _{GS} = - 10 V	I _D = - 4.7 A, V _{DS} = - 48 V, see fig. 6 and 13 ^b	-	-	12	nC
Gate-Source Charge	Q _{gs}			-	-	3.8	
Gate-Drain Charge	Q _{gd}			-	-	5.1	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 30 V, I _D = - 4.7 A, R _G = 24 Ω, R _D = 4.0 Ω, see fig. 10 ^b		-	11	-	ns
Rise Time	t _r			-	63	-	
Turn-Off Delay Time	t _{d(off)}			-	9.6	-	
Fall Time	t _f			-	31	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	- 5.2	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	- 21	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = - 5.2 A, V _{GS} = 0 V ^b		-	-	- 5.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = - 4.7 A, dI/dt = 100 A/μs ^b		-	80	160	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.096	0.19	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

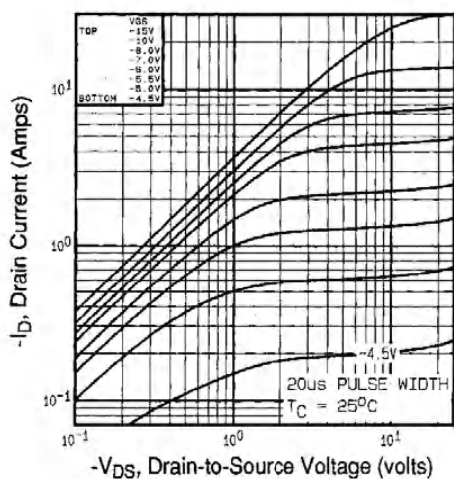
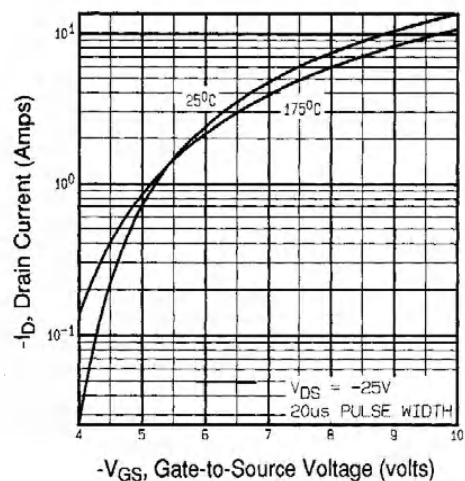
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted
Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$ 

Fig. 3 - Typical Transfer Characteristics

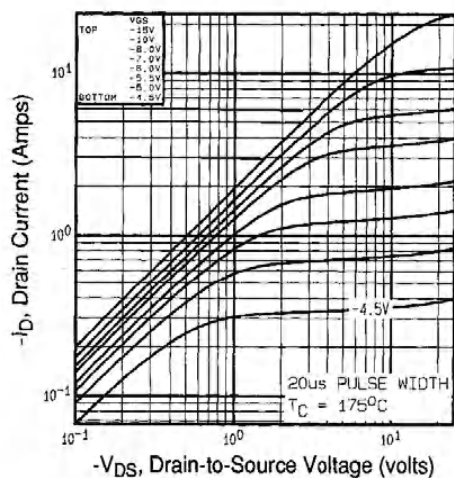
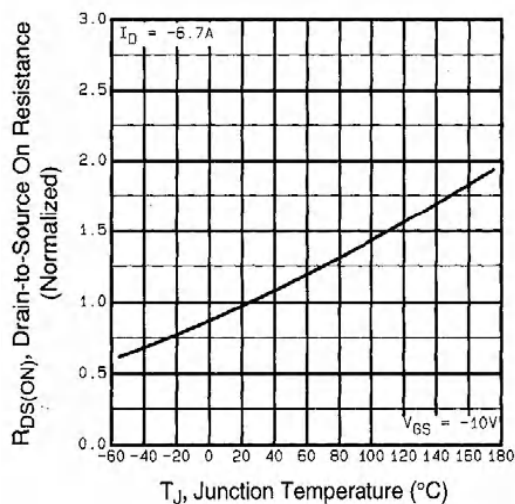
Fig. 2 - Typical Output Characteristics, $T_C = 175\text{ }^{\circ}\text{C}$ 

Fig. 4 - Normalized On-Resistance vs. Temperature

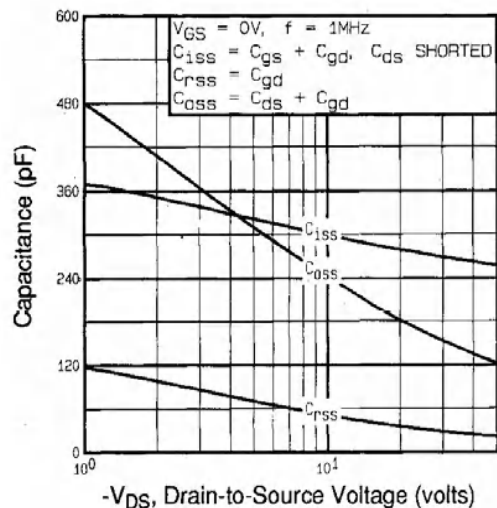


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

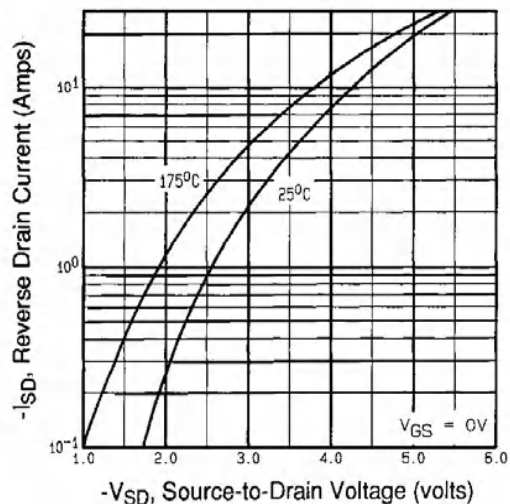


Fig. 7 - Typical Source-Drain Diode Forward Voltage

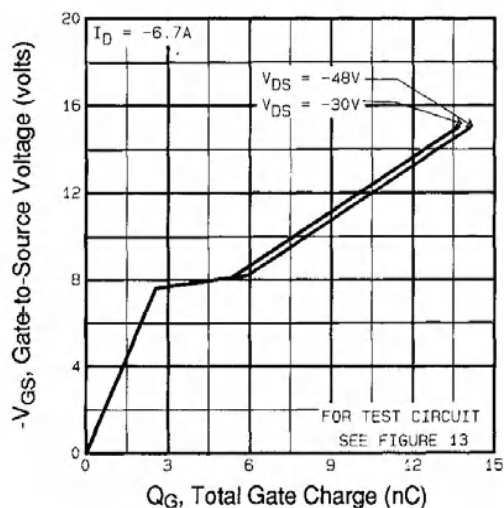


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

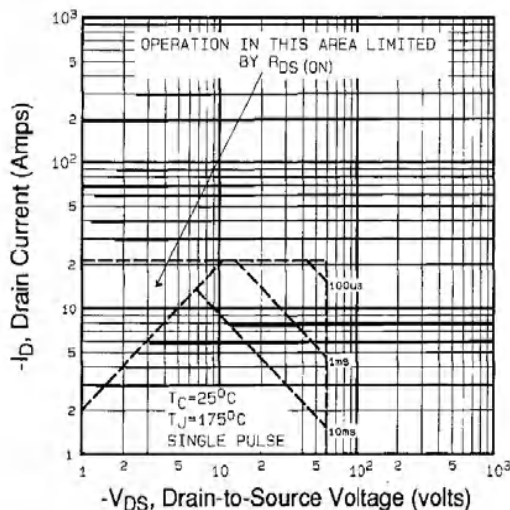


Fig. 8 - Maximum Safe Operating Area

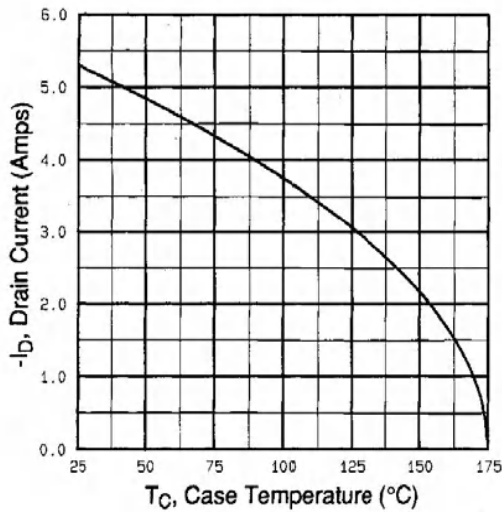


Fig. 9 - Maximum Drain Current vs. Case Temperature

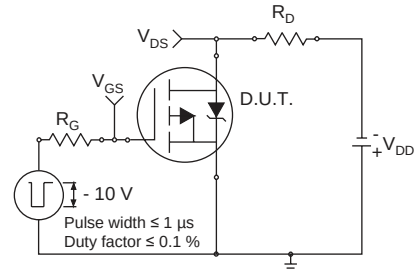


Fig. 10a - Switching Time Test Circuit

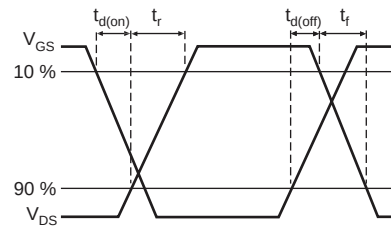


Fig. 10b - Switching Time Waveforms

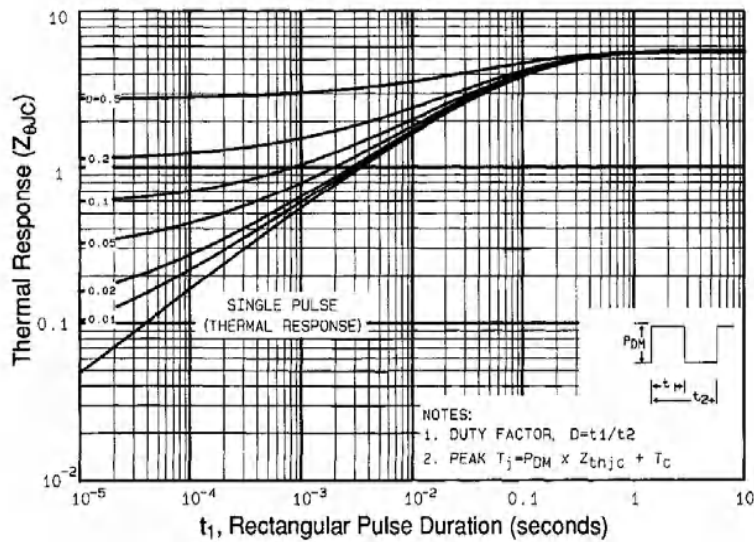


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

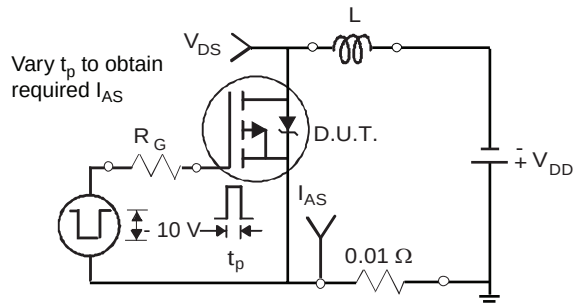


Fig. 12a - Unclamped Inductive Test Circuit

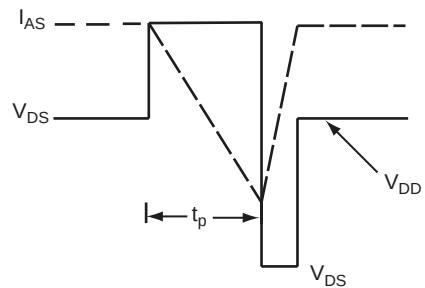


Fig. 12b - Unclamped Inductive Waveforms

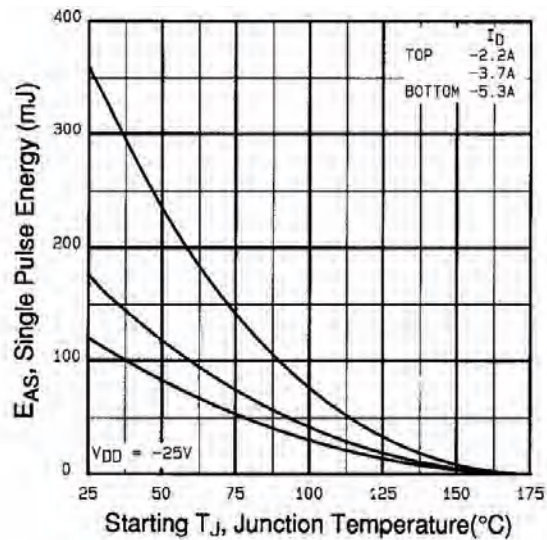


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

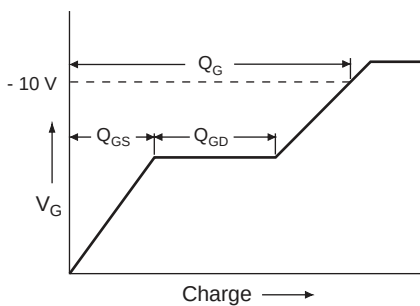


Fig. 13a - Basic Gate Charge Waveform

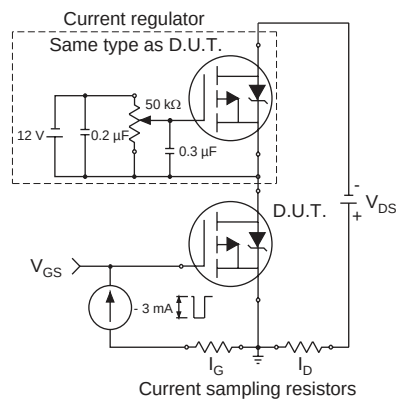
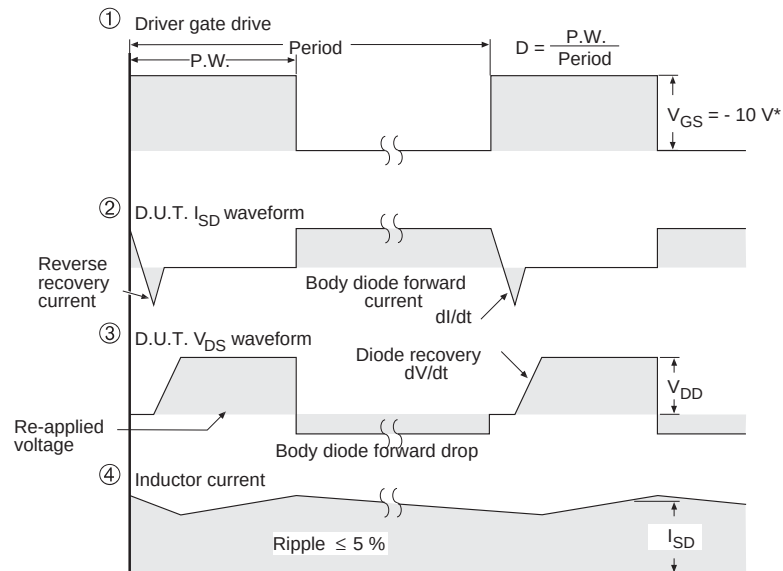
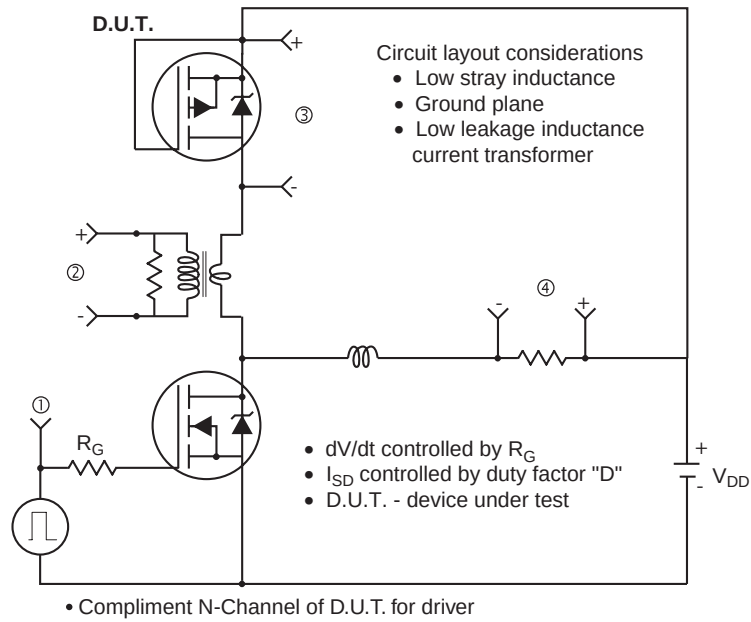


Fig. 13b - Gate Charge Test Circuit

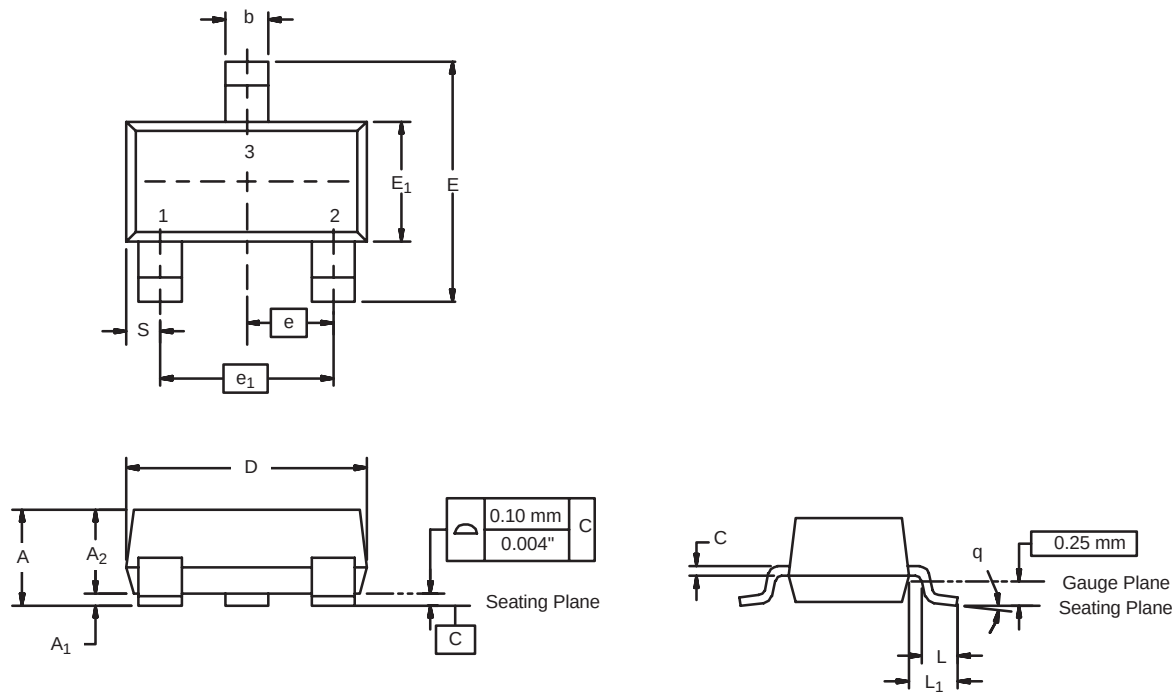
Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5 V$ for logic level and $-3 V$ drive devices

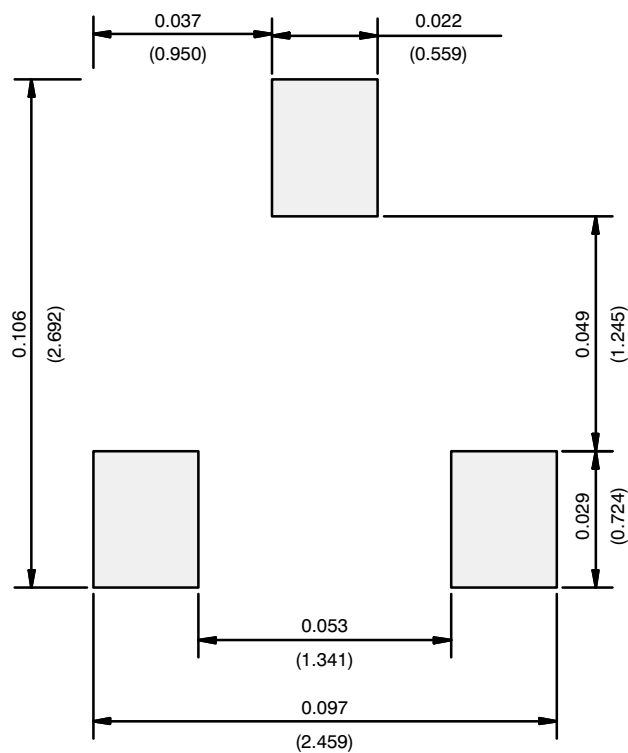
Fig. 14 - For P-Channel

SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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